

Ruttonsha International Rectifier Ltd. POWER MODULES (FAST RECOVERY)

IRK. 196. SERIES Diode/Diode

FEATURES

- High voltage.
- Electrically isolated base plate.
- 3000 V_{RMS} isolating voltage.
- Industrial standard package.
- Simplified mechanical designs, rapid assembly.
- High surge capability.
- Large creepage distances.
- Aluminum Nitride

DESCRIPTION

This IRK series of Power Modules uses power diodes in three basic configurations. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges. These modules are intended for general purpose applications such as battery chargers, welders and plating equipment.

MAJOR RATINGS & CHARACTERISTICS

Parameters		IRK.196	Units
L _{F(AV)}	$@ T_{c} = 100^{\circ}C$	195	Α
I _{F(RMS)}		305	Α
I _{FSM}	@ 50 Hz	4750	А
[² t	@ 50 Hz	113	k A ²s
I²√t		1130	kA²√s
V _{RRM} range		600	V
T _J		-40 to 125	°C

POWER MODULES (FAST RECOVERY)

IRK. 196. SERIES

ELECTRICAL SPECIFICATION VOLTAGE RATINGS

Type Number	Voltage Code	V _{RRM} , max. repetitive peak reverse and off-state voltage blocking voltage	V _{RSM} , max. non-repetitive peak reverse voltage V	I _{RRM} max. @ 150°C mA
	04	400	500	30
IRK.196	06	600	700	30

FORWARD CONDUCTION

	Parameters	IRK.196	Units	Condition	S	
[_{F(AV)}	Max. average forward current	195	Α	180°C conduction, half sine wave		
	@ case temperature	100	٥C			
[F(RMS)	Max. RMS forward current	305	Α	as AC switch		
I _{FSM}	Max. peak, one cycle forward non-repetitive surge current	4750	Α	t = 10ms	Sinusoidal half wave,	
l²t	Maximum I ² t for fusing	113	kA²s	t = 10ms	Initial $T_J = T_J$ max.	
l²√t	Maximum l²√t for fusing	1130	kA²√s	t = 0.1 to 10ms. No voltage reapplied.		
V _{F(TO)}	Threshold voltage	0.75	V	$T_J = T_J \text{ max.}$		
r _t	Forward slope resistance	0.92	mΩ	$T_{J} = T_{J} max.$		
V _{FM}	Max. forward voltage drop	1.65	V	$I_{FM} = \pi \times I_{F(AV)}$, $T_J = T_J \text{ max., } 180^{\circ} \text{ conduction}$ AV. power = $V_{F(TO)} \times I_{F(AV)} + r_1 \times (I_{F(RMS)})^2$		
t _{rr}	Maximum reverse recovery time	500	ns	Tj= 25°C, -diF/dt = 25A/μs I _{FM} = ττ x I _F (AV)		

POWER MODULES (FAST RECOVERY)

IRK.196. SERIES

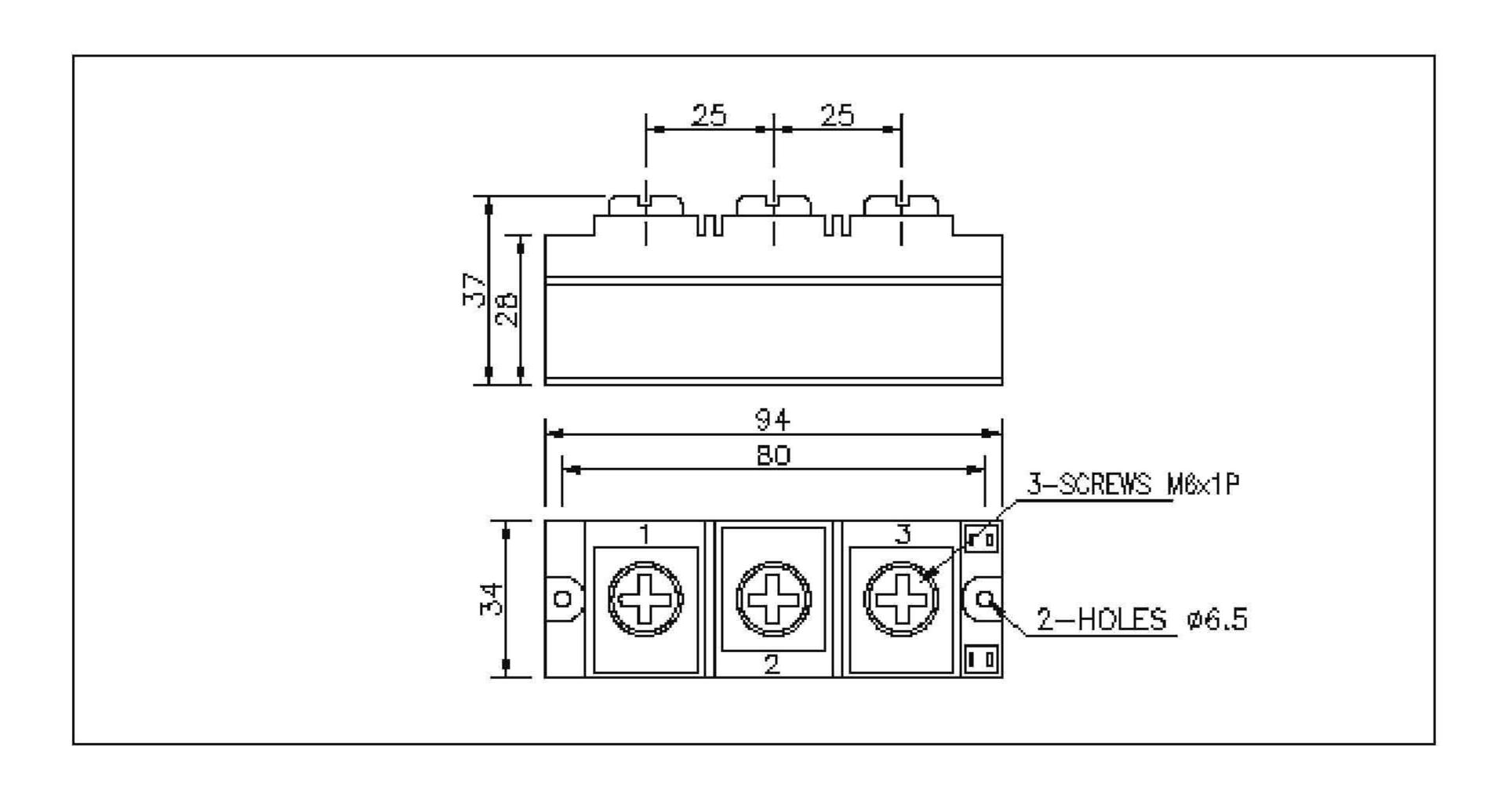
THERMAL AND MECHANICAL SPECIFICATIONS

	Parameters		IRK.196	Units	Conditions	
$T_{\rm J}$	Junction operating temperature		-40 to 125	٥C		
T _{stg}	Storage temperature range		-40 to 150	٥C		
R _{thj-c}	Max. internal the junction to case	ermal resistance,	0.20	K/W	IRKD/IRKJ/IRKC	Per junction, DC operation
R _{thC-S}	Thermal resistance, case to heatsink		0.035	K/W	Mounting surface flat, smooth and greased	
T	Mounting torque ±10%	Module to heatsink Busbar to module	4 to 6 4 to 6	Nm Nm	A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound.	
Wt	Approximate we	ight	350	g		

BLOCKING

		Parameter	IRK.196	Units	Conditions
	I _{RRM}	Max. peak reverse leakage current	50	mA	$T_{J} = 150^{\circ}C$
Ī	V _{INS}	RMS isolation voltage	3000	٧	50 Hz, circuit to base, all terminals shorted, t=1sec

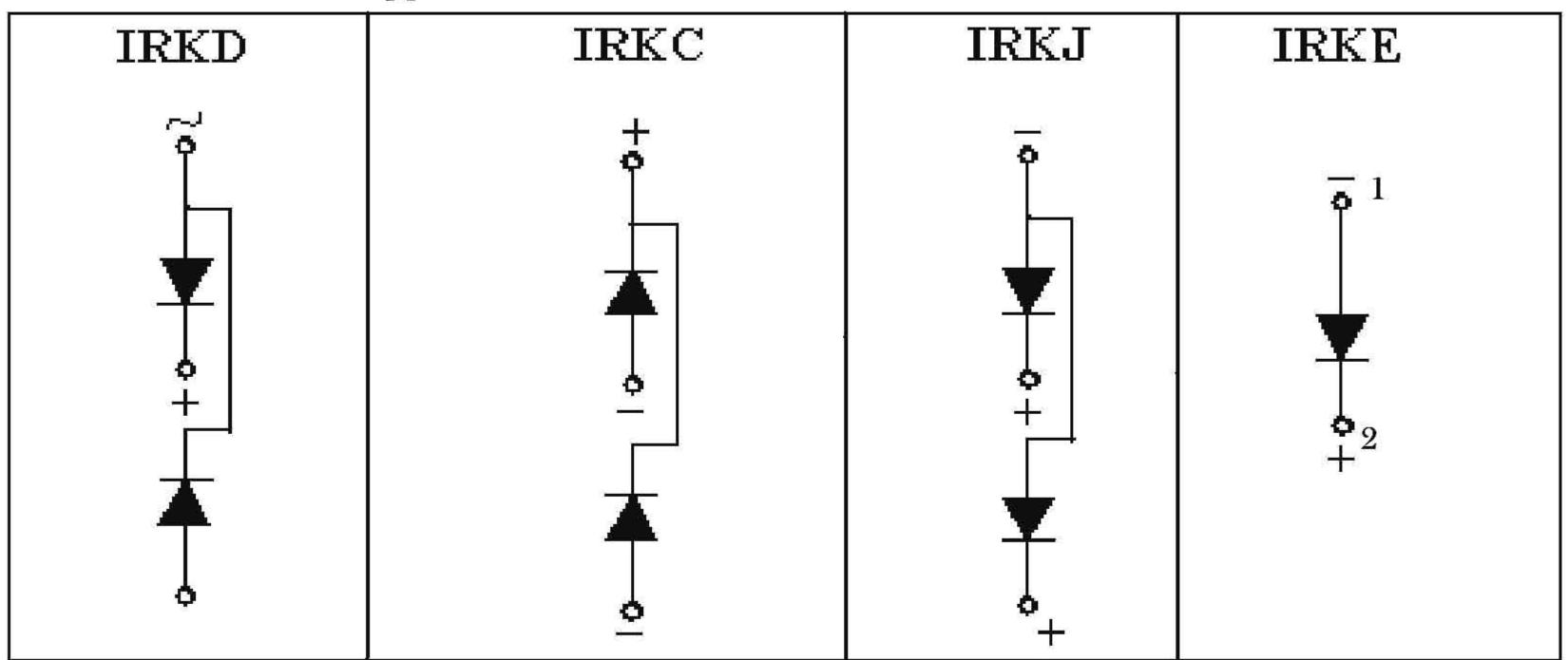
OUTLINE DIAGRAM



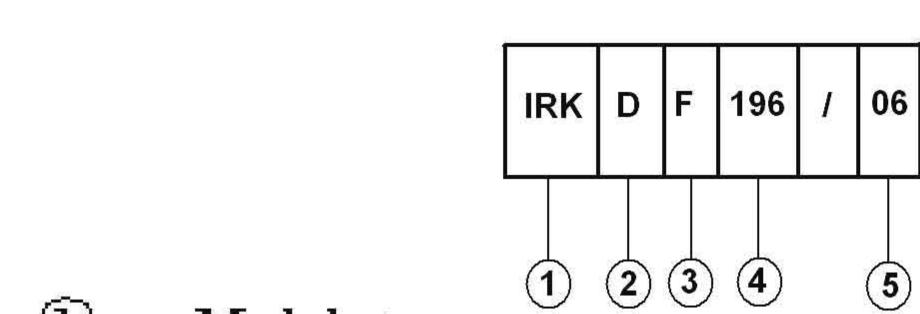
POWER MODULES (FAST RECOVERY)

IRK.196. Series

Circuit Configuration Table



Ordering Information Table



- 1 Module type:
- ② Circuit configuration (See Circuit Configuration table)
- (3) F For fast recovery
- (4) Current Code
- 5 Voltage Code (See Voltage Ratings table)